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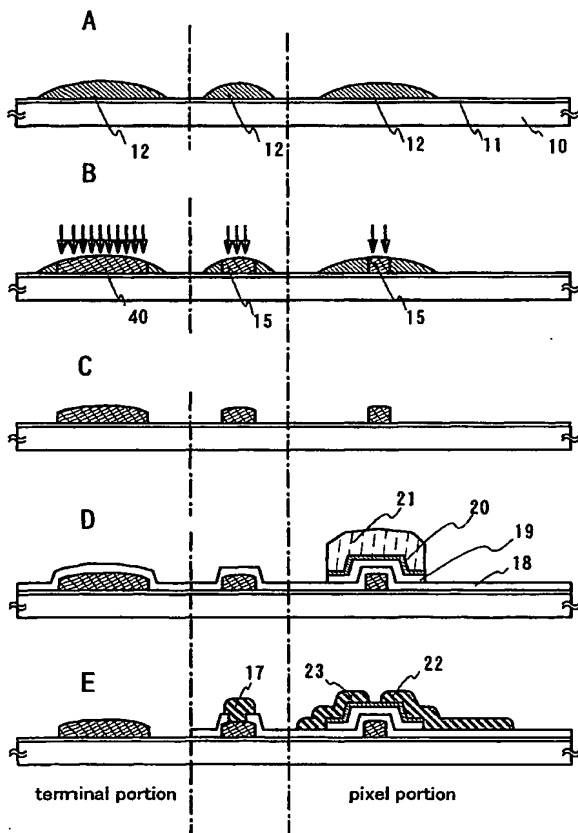
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(54) Title: ELECTRIC APPLIANCE, SEMICONDUCTOR DEVICE, AND METHOD FOR MANUFACTURING THE SAME



(57) Abstract: In the present circumstances, a film formation method of using spin coating in a manufacturing process is heavily used. As increasing the substrate size in future, the film formation method of using spin coating becomes at a disadvantage in mass production since a mechanism for rotating a large substrate becomes large, and there is many loss of material solution or waste liquid. According to the present invention, in a manufacturing process of a semiconductor device, a microscopic wiring pattern can be realized by delivering selectively photosensitive conductive material solution by droplet discharging, exposing selectively to laser light or the like, and developing. The present invention can reduce drastically costs since a patterning process can be shortened and an amount of material in a process of forming a conductive pattern can be reduced. Accordingly, the present invention can be applied to manufacture a large substrate.



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